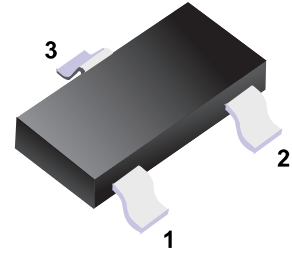
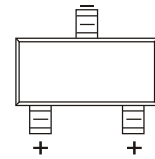


• Plastic-Encapsulate Diodes
BAV170
FEATURES

- Low Leakage Current
- High Switching Speed

APPLICATION

- Low-leakage Current Applications

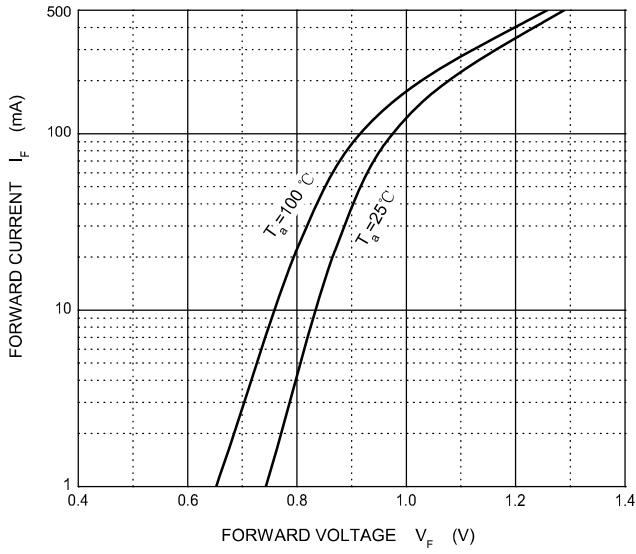

MARKING:JXW

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	85	V
V_R	DC Blocking Voltage	75	V
I_F	Forward Current(single diode)	215	mA
	Forward Current(double diode)	125	
I_{FRM}	Repetitive Peak Forward Current	500	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current@ $t = 8.3\text{ms}$	1.0	A
P_D	Power Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	500	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

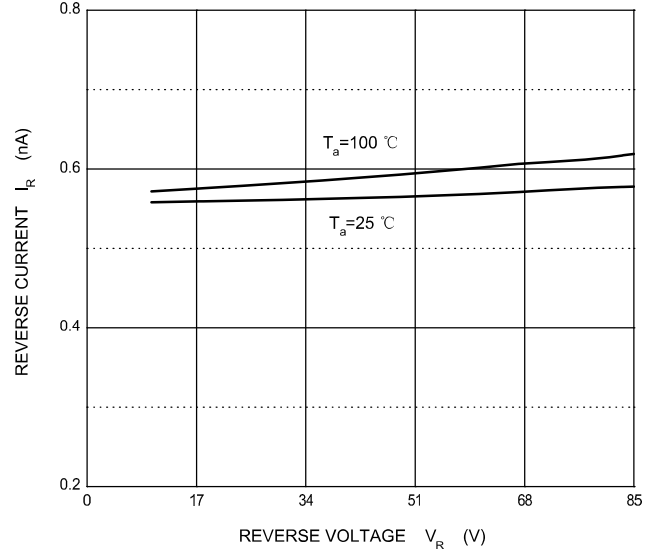
ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	75			V
Reverse current	I_R	$V_R=75\text{V}$			5	nA
Forward voltage	V_F	$I_F=1\text{mA}$			0.9	V
		$I_F=10\text{mA}$			1	
		$I_F=50\text{mA}$			1.1	
		$I_F=150\text{mA}$			1.25	
Total capacitance	C_{tot}	$V_R=0, f=1\text{MHz}$		2		pF
Reverse recovery time	t_{rr}	$I_F= I_R=10\text{mA}, I_{rr}=0.1 \times I_R, R_L=100\Omega$			3	μs

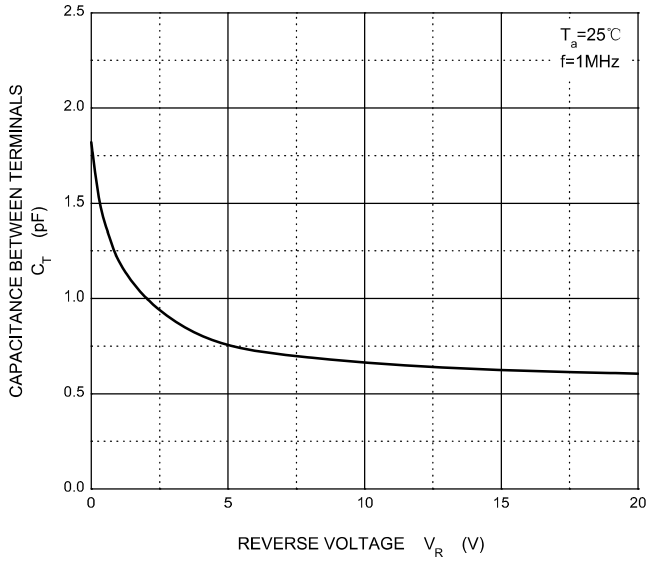
Forward Characteristics



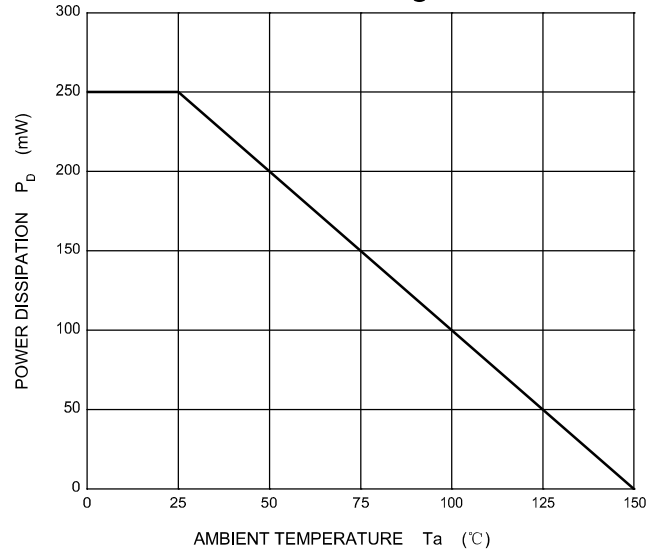
Reverse Characteristics



Capacitance Characteristics

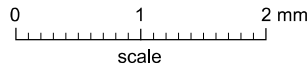
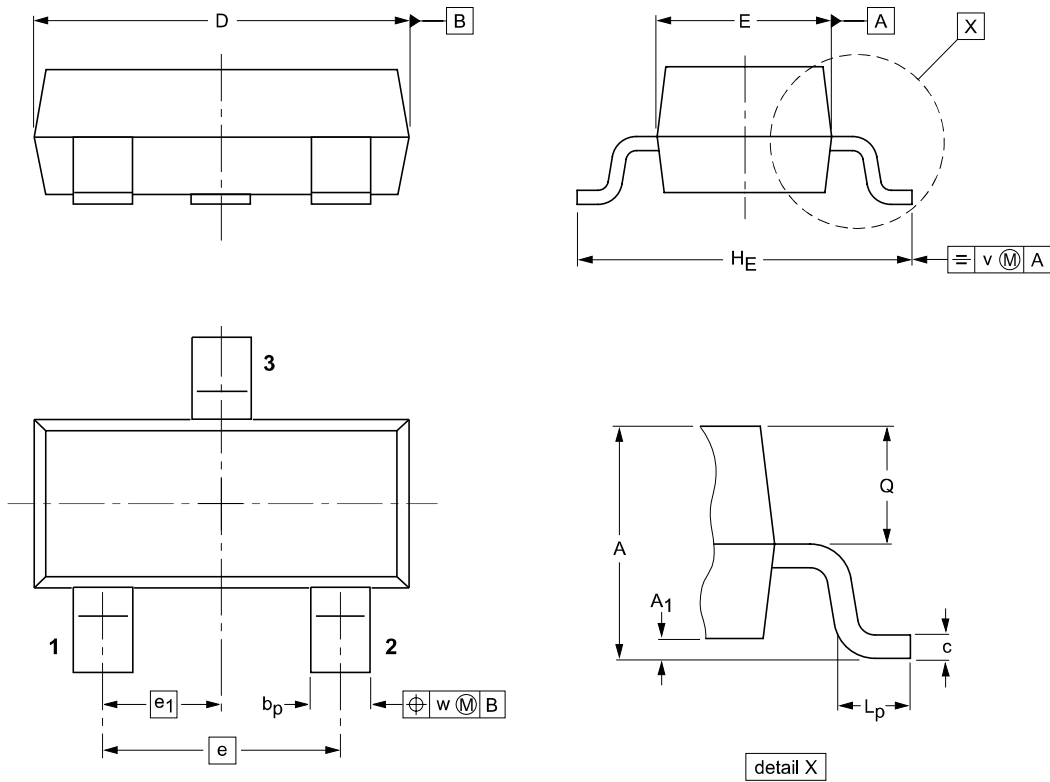


Power Derating Curve



Package Outline

SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

Summary of Packing Options

Package	Packing Description	Packing Quantity	Industry Standard
SOT-23	Tape/Reel,7"reel	3000	EIA-481-1